

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|---|-------------------|------------------|
| 1 | 852 | (((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor) | USPAT | 2003/10/30 14:31 |
| 2 | 28 | (((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor)) and (second adj power) | USPAT | 2003/10/30 14:31 |
| 3 | 92 | (((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor)) and anti\$!reflective | USPAT | 2003/10/30 14:31 |
| 4 | 680 | (((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor)) and (photo\$!resist or resist) | USPAT | 2003/10/30 14:31 |
| 5 | 1 | (((((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor) | EPO; JPO; DERWENT | 2003/10/30 14:32 |
| 6 | 357 | semiconductor and plasma and power and (photo\$!resist or resist) | EPO; JPO; DERWENT | 2003/10/30 14:32 |
| 7 | 9 | (semiconductor and plasma and power and (photo\$!resist or resist)) and (anti\$!reflective or ARC!) | EPO; JPO; DERWENT | 2003/10/30 14:33 |
| 8 | 10 | (semiconductor and plasma and power and (photo\$!resist or resist)) and (anti\$!reflective or ARC! or BARC) | EPO; JPO; DERWENT | 2003/10/30 14:33 |
| - | 6 | ((("6489632") or ("6426016") or ("6355557") or ("6180533") or ("6074959") or ("6054377"))).PN. | USPAT | 2003/06/24 09:48 |
| - | 13 | ((("6489632") or ("6426016") or ("6355557") or ("6180533") or ("6074959") or ("6054377") or ("5726499") or ("5710067") or ("5242532") or ("5242536") or ("5312717") or ("5662770") or ("5843226"))).PN. | USPAT | 2003/06/24 10:01 |
| - | 29912 | semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)) | USPAT | 2003/06/24 10:04 |
| - | 15628 | (semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching))) and plasma | USPAT | 2003/06/24 10:04 |
| - | 3739 | (semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching))) and (plasma same power) | USPAT | 2003/06/24 10:05 |
| - | 3176 | ((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching))) and (plasma same power)) and (Watt or W!) | USPAT | 2003/06/24 10:04 |
| - | 19830 | semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching)) | USPAT | 2003/06/24 10:05 |

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|---|-------|--|-------|---------------------|
| - | 2821 | (semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power) | USPAT | 2003/06/24 10:06 |
| - | 2421 | ((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and (Watt or W!) | USPAT | 2003/06/24 10:07 |
| - | 1163 | ((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt | USPAT | 2003/06/24 10:07 |
| - | 823 | ((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3) | USPAT | 2003/06/24 10:08 |
| - | 823 | ((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor | USPAT | 2003/06/24 10:08 |
| - | 592 | ((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor) and 438/\$.ccls. | USPAT | 2003/10/30 14:17 |
| - | 38 | ((semiconductor and (((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) with (etch or etching))) and (plasma same power)) and Watt) and (CF?sub.4 or inert or CHF?sub.3)) and semiconductor) and 438/706.ccls. | USPAT | 2003/06/24 10:12 |
| - | 33686 | ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching) | USPAT | 2003/06/26 15:21 |
| - | 2089 | ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)) same power | USPAT | 2003/06/26 15:22 |
| - | 1051 | ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)) same power) same (Cl?sub.2 or chlorine ro CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or Ar! or argon) | USPAT | 2003/06/26 15:24 |
| - | 20 | ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2) same (etch or etching)) same power) same (Cl?sub.2 or chlorine ro CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or Ar! or argon)) and (second adj power) | USPAT | 2003/06/26 15:25 |